

CLAIMS

What is claimed is:

1. A method of fabricating a heterojunction bipolar transistor comprising:
growing a base layer comprising gallium, indium, arsenic, and nitrogen
5 over an n-doped GaAs collector from a gallium, indium, arsenic, and nitrogen
source, wherein the base layer is p-doped with carbon from an external carbon
source; and
growing an n-doped emitter layer over the base layer.
2. The method of Claim 1, wherein the external carbon source is carbon
10 tetrabromide or carbon tetrachloride.
3. The method of Claim 2, wherein the gallium source is selected from
trimethylgallium and triethylgallium.
4. The method of Claim 3, wherein the nitrogen source is ammonia or
dimethylhydrazine.
- 15 5. The method of Claim 4, wherein the ratio of the arsenic source to the gallium
source is about 2.0 to about 3.5.
6. The method of Claim 5, wherein the base is grown at a temperature of less than
750°C.
7. The method of Claim 6, wherein the base is grown at a temperature of about
20 500°C to about 600°C.

8. The method of Claim 6, wherein the base layer comprises a layer of the formula $\text{Ga}_{1-x}\text{In}_x\text{As}_{1-y}\text{N}_y$, wherein x and y are each, independently, about 1.0×10^{-4} to about 2.0×10^{-1} .
- 5 9. The method of Claim 8, wherein x is about equal 3y.
10. The method of Claim 8, wherein the collector is GaAs and the emitter is InGaP, AlInGaP, or AlGaAs and the transistor is a double heterojunction dipolar transistor.
- 10 11. The method of Claim 8, further comprising the step of growing an n-doped first transitional layer over the collector and disposed between the base and the collector, wherein the first transitional layer has a graded band gap or a band gap that is smaller than the band gap of the collector.
12. The method of Claim 11, wherein the first transitional layer is selected from the group consisting of GaAs, InGaAs, or InGaAsN.
- 15 13. The method of Claim 12, further comprising the step of growing an second transitional layer over the base, wherein the second transitional layer has a first surface contiguous with a surface of a first surface of the base and a second surface contiguous with a surface of the emitter, and wherein the second transitional layer has a doping concentration at least one order of magnitude less than the doping concentration of the emitter.
- 20 14. The method of Claim 13, wherein the second transitional layer is selected from the group consisting of GaAs, InGaAs, or InGaAsN.

15. The method of Claim 14, wherein the first transitional layer, the second transitional layer, or both the first and the second transitional layer have a doping spike.
16. The method of Claim 14, further comprising the step of growing a latticed
5 matched layer over the collector, wherein the lattice matched layer has a first surface contiguous with a first surface of the collector and a second surface contiguous with a second surface of the first transitional layer.
17. The method of Claim 16, wherein the lattice matched layer is InGaP.